

N-Channel 200 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	0.090 at $V_{GS} = 10$ V	19
	0.105 at $V_{GS} = 6$ V	17.5

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

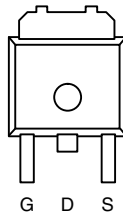


RoHS
COMPLIANT

APPLICATIONS

- Primary Side Switch

TO-252

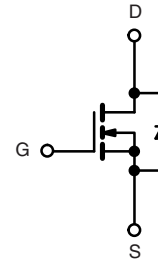


Top View

Drain Connected to Tab

Ordering Information:

SUD19N20-90-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	200	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I _D	19	A
	T _C = 125 °C		11	
Pulsed Drain Current		I _{DM}	40	
Continuous Source Current (Diode Conduction)		I _S	19	
Avalanche Current		I _{AS}	19	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	18	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	136 ^b	W
	T _A = 25 °C		3 ^a	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	15	°C/W
		Steady State	40	
Junction-to-Case (Drain)	R_{thJC}	0.85	1.1	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

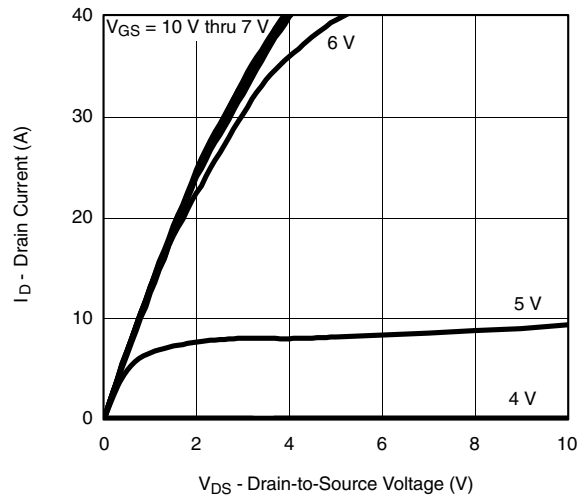
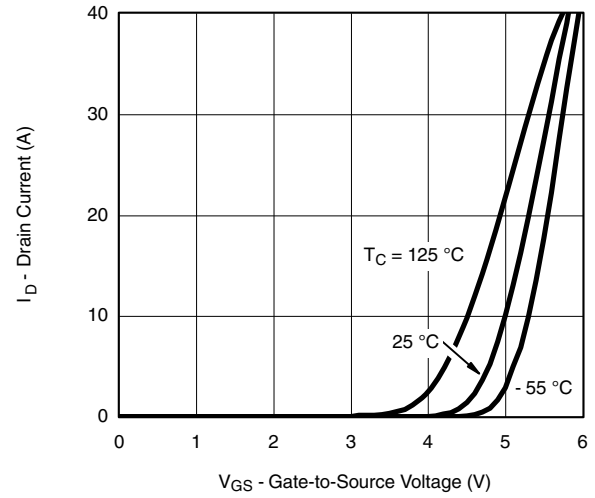
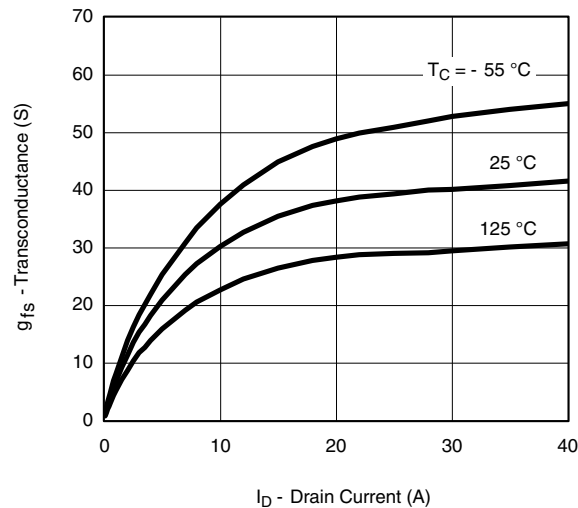
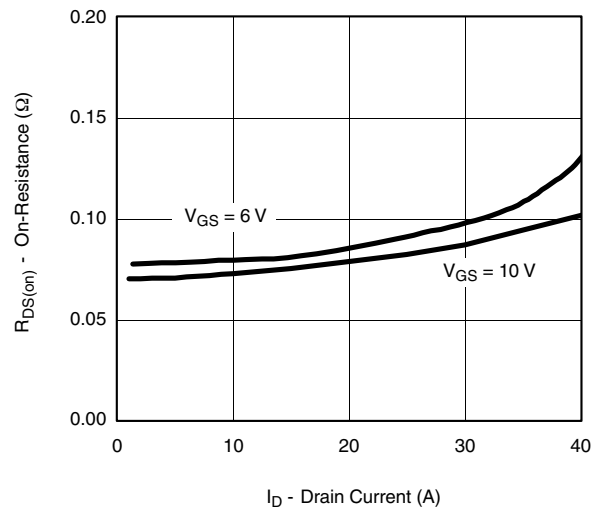
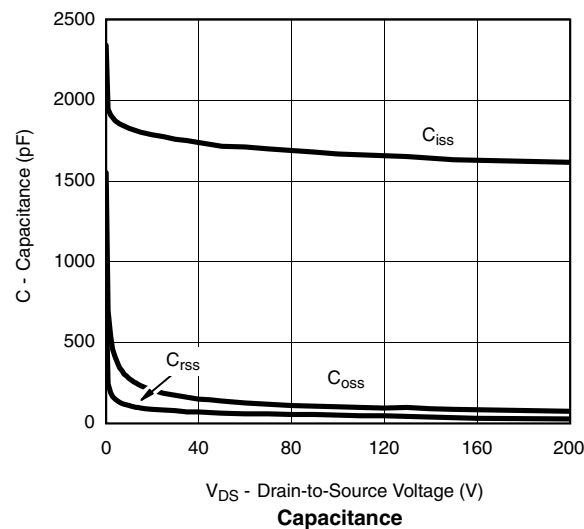
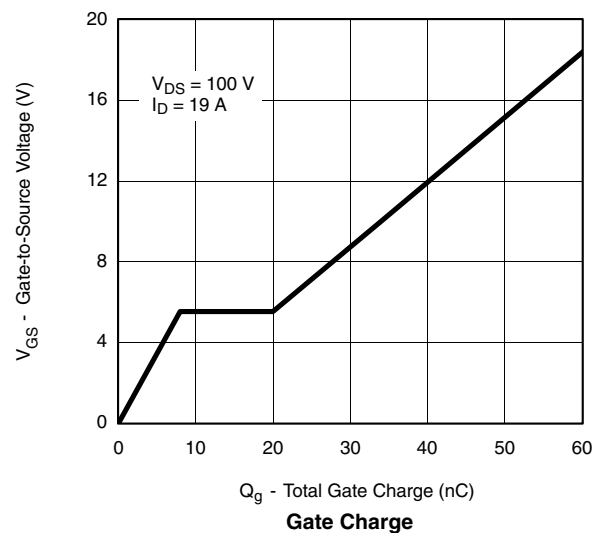
b. See SOA curve for voltage derating.

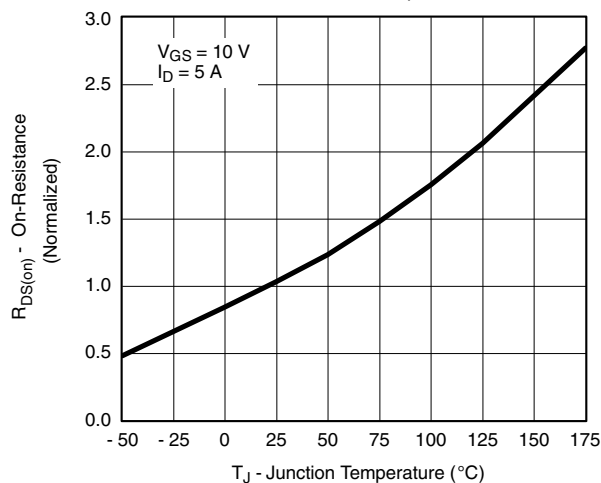
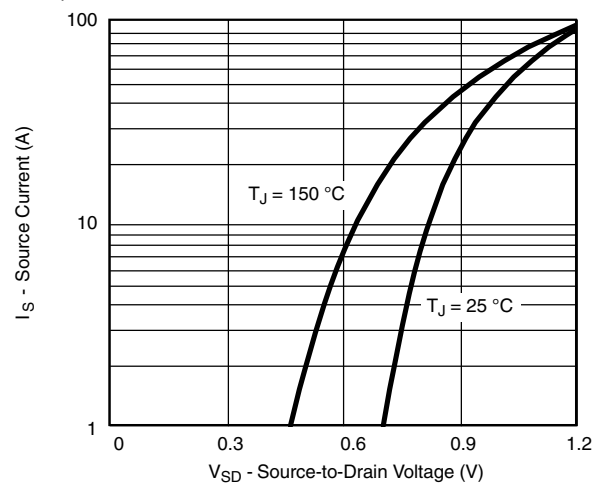
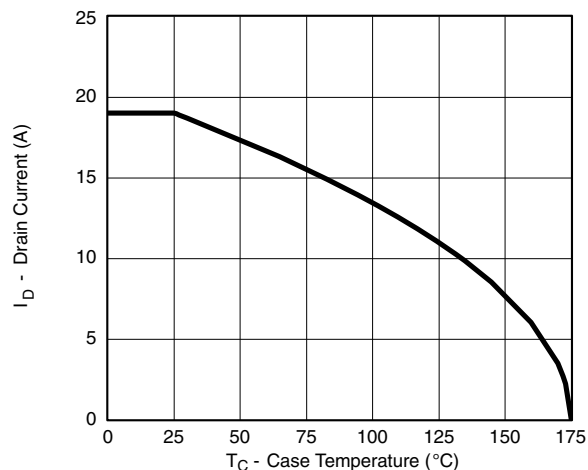
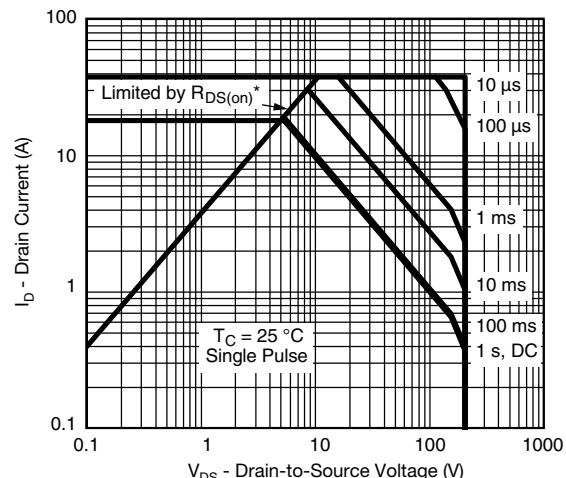
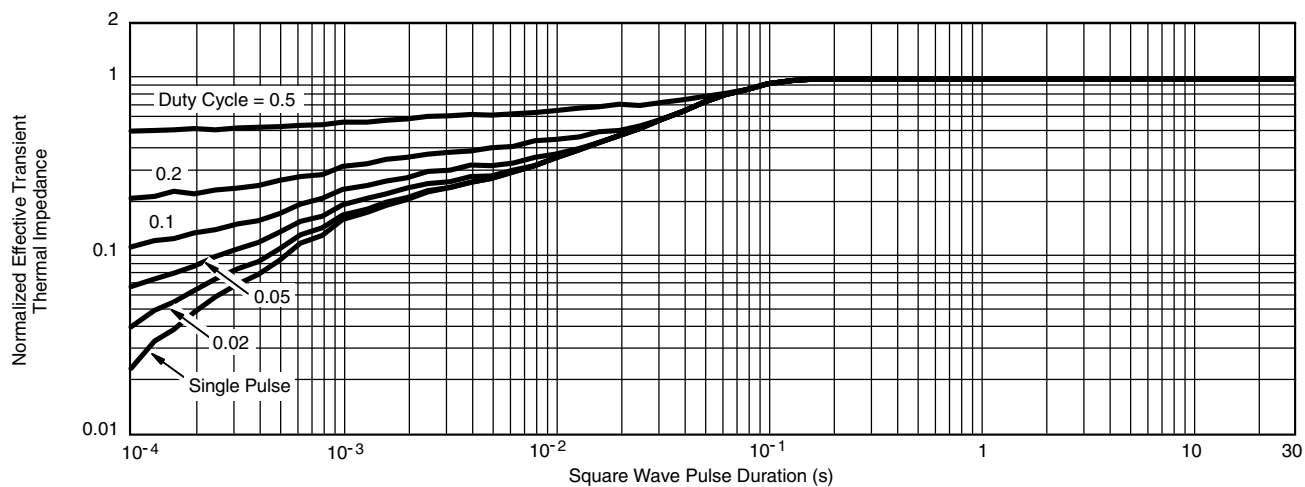
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	200			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2		4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V			1	μA
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A		0.075	0.090	Ω
		V _{GS} = 10 V, I _D = 5 A, T _J = 125 °C			0.190	
		V _{GS} = 10 V, I _D = 5 A, T _J = 175 °C			0.260	
		V _{GS} = 6 V, I _D = 5 A		0.082	0.105	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 19 A		35		S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, F = 1 MHz		1800		pF
Output Capacitance	C _{oss}			180		
Reverse Transfer Capacitance	C _{rss}			80		
Total Gate Charge ^c	Q _g	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 19 A		34	51	nC
Gate-Source Charge ^c	Q _{gs}			8		
Gate-Drain Charge ^c	Q _{gd}			12		
Gate Resistance	R _g		0.5		2.9	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 100 V, R _L = 5.2 Ω I _D ≅ 19 A, V _{GEN} = 10 V, R _g = 2.5 Ω		15	25	ns
Rise Time ^c	t _r			50	75	
Turn-Off Delay Time ^c	t _{d(off)}			30	45	
Fall Time ^c	t _f			60	90	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)						
Pulsed Current	I _{SM}				50	A
Diode Forward Voltage ^b	V _{SD}	I _F = 19 A, V _{GS} = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 19 A, dI/dt = 100 A/μs		180	250	ns

Notes:

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
c. Independent of operating temperature.

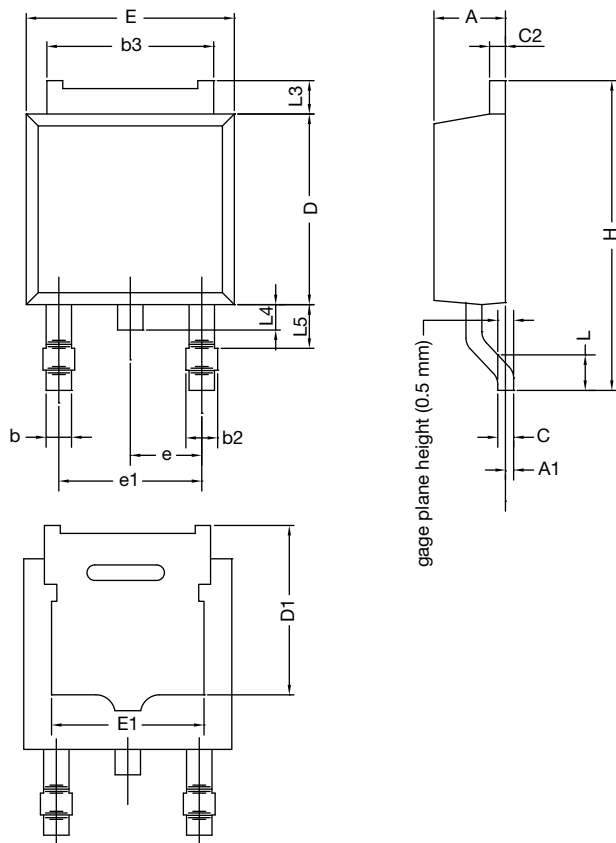
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****THERMAL RATINGS****Maximum Avalanche Drain Current vs. Case Temperature*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71767.

TO-252AA CASE OUTLINE

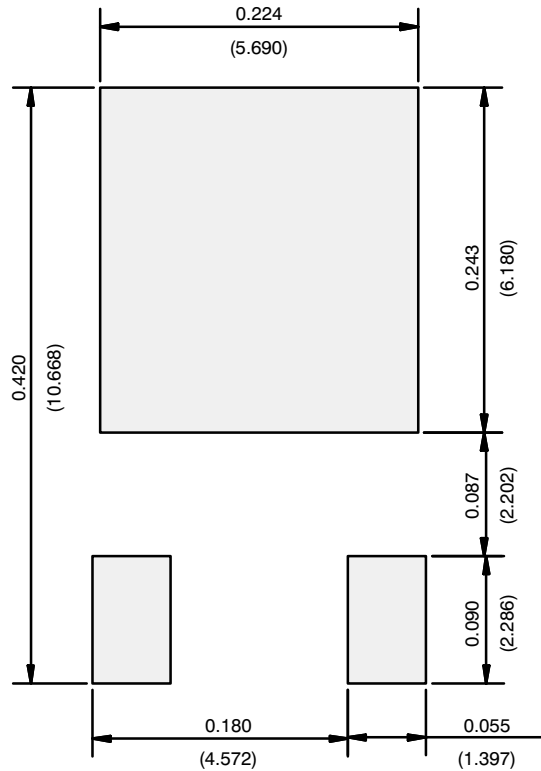


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12				
DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru